
2SK1402, 2SK1402A

Silicon N-Channel MOS FET

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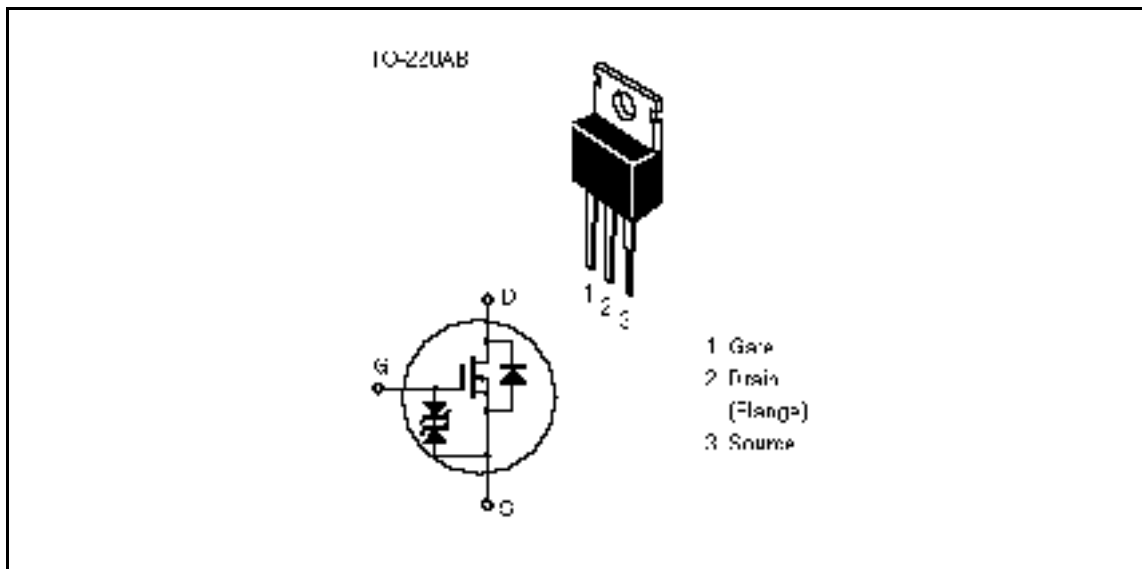
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



2SK1402, 2SK1402A

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1402	V_{DSS}	600	V
	2SK1402A		650	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	4	A
Drain peak current		$I_{D(pulse)}^{*1}$	16	A
Body to drain diode reverse drain current		I_{DR}	4	A
Channel dissipation		P_{ch}^{*2}	50	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

Notes: 1. PW 10 μs, duty cycle 1%

2. Value at T_c = 25°C

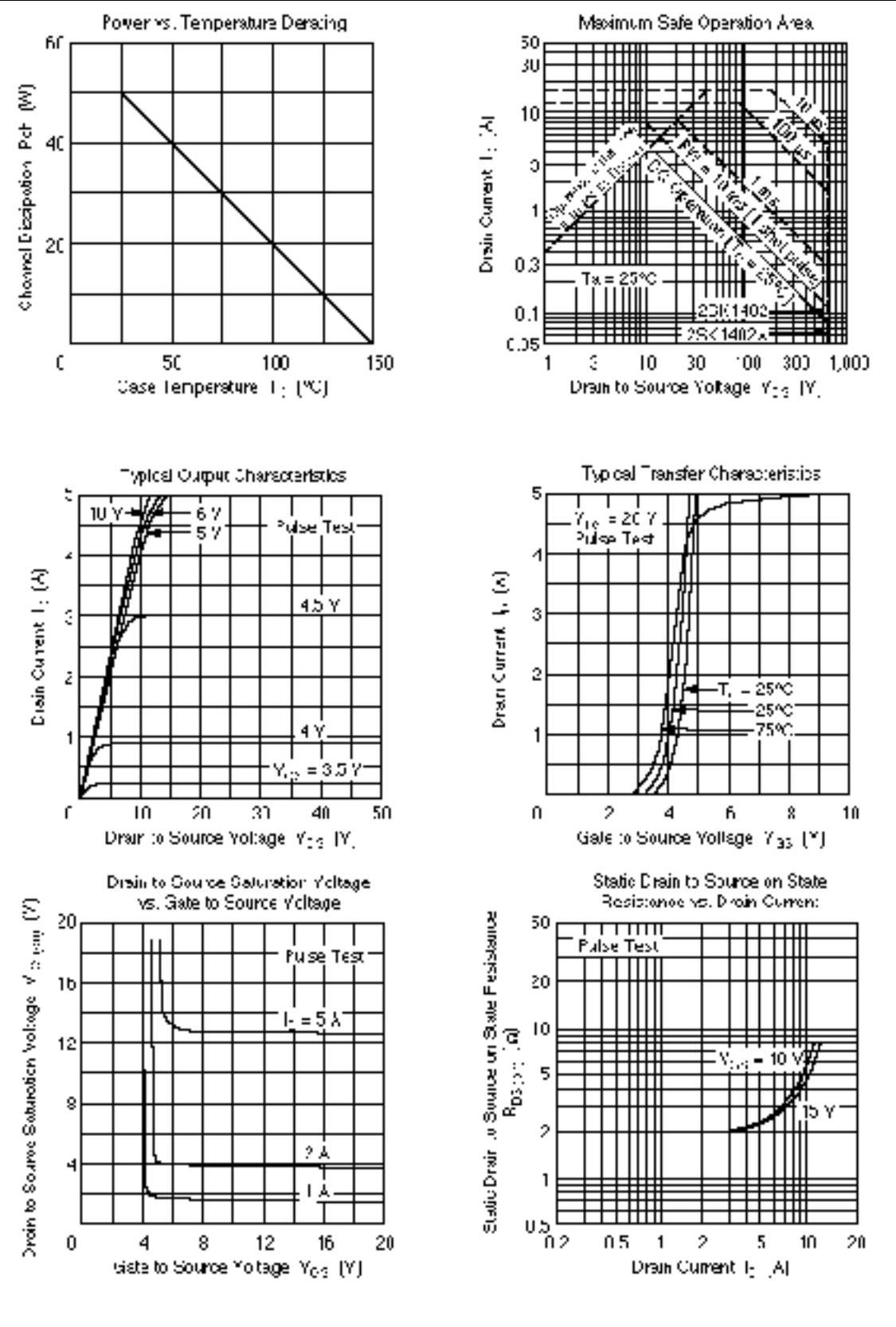
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Electrical Characteristics (Ta = 25°C)

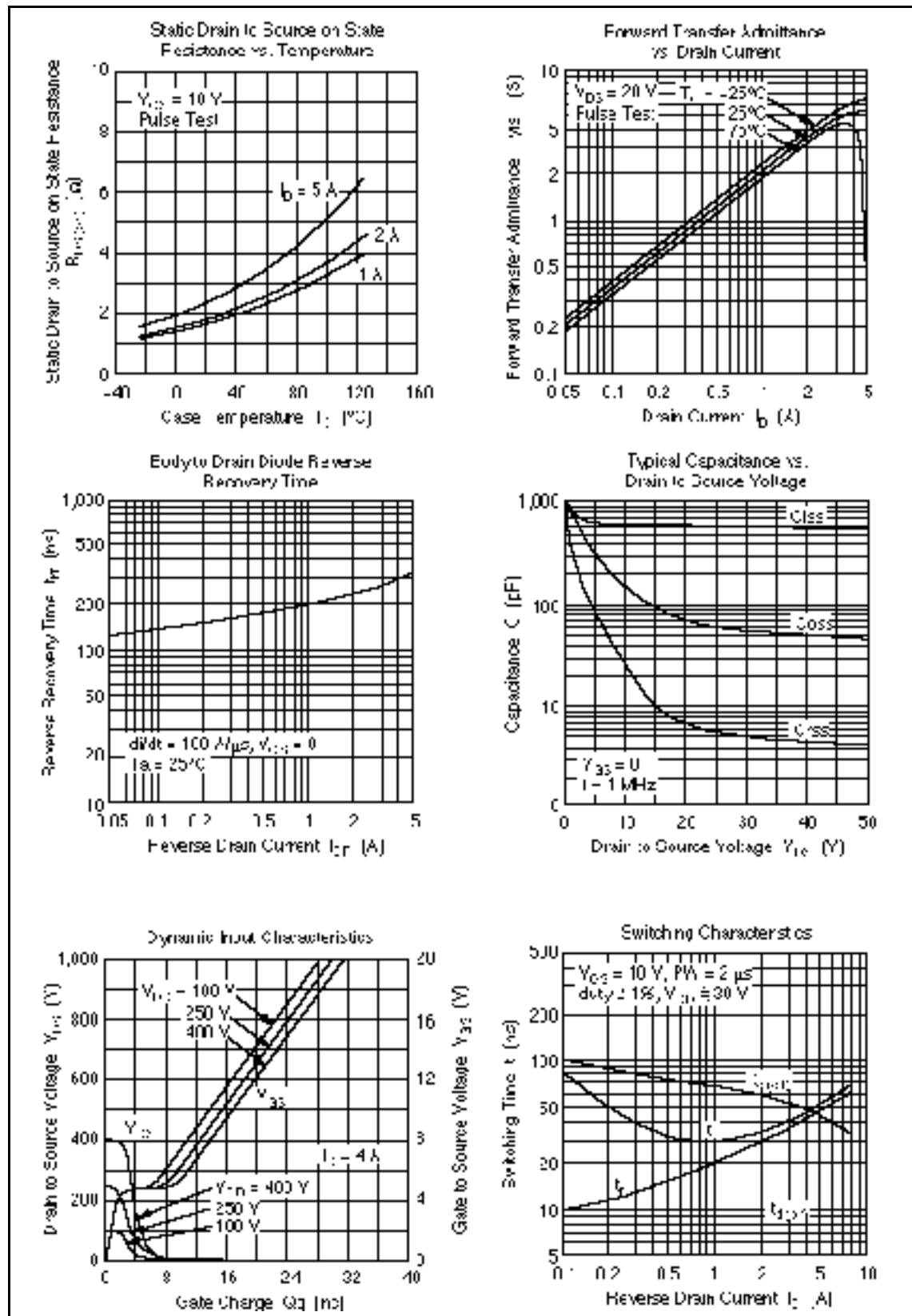
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	K1402 K1402A	$V_{(BR)DSS}$	600 650	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	K1402 K1402A	I_{DSS}	—	—	250	μA	$V_{DS} = 500 \text{ V}$, $V_{GS} = 0$ $V_{DS} = 550 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	K1402 K1402A	$R_{DS(on)}$	— —	1.8 2.0	2.4 2.6		$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		$ y_{fs} $	2.2	3.5	—	S	$I_D = 2 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	600	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$,
Output capacitance		C_{oss}	—	140	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	25	—	pF	
Turn-on delay time		$t_{d(on)}$	—	8	—	ns	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$,
Rise time		t_r	—	30	—	ns	$R_L = 15$
Turn-off delay time		$t_{d(off)}$	—	60	—	ns	
Fall time		t_f	—	35	—	ns	
Body to drain diode forward voltage		V_{DF}	—	0.9	—	V	$I_F = 4 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	300	—	ns	$I_F = 4 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

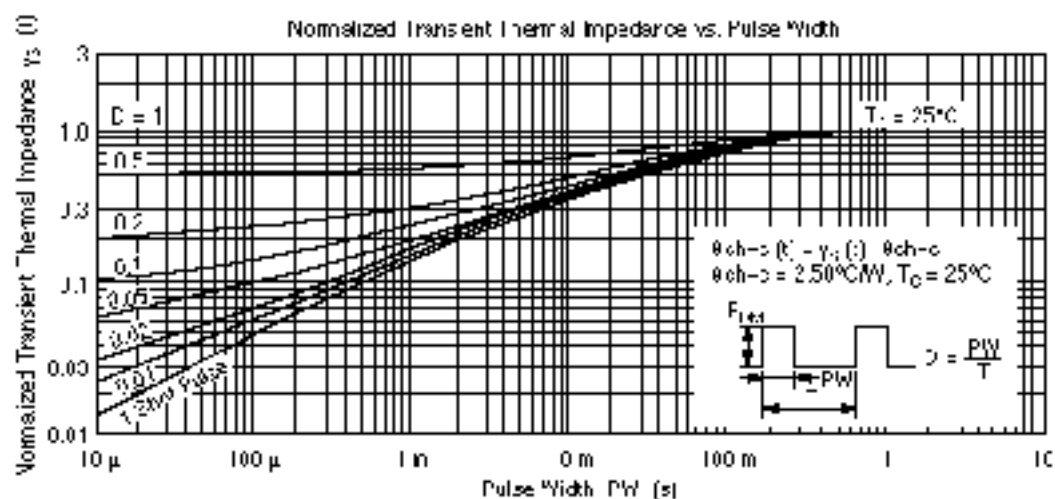
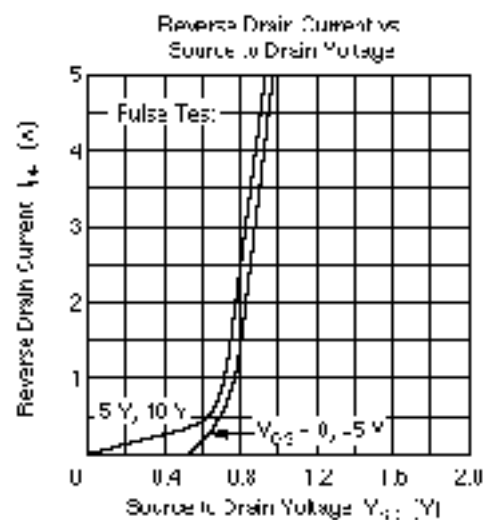
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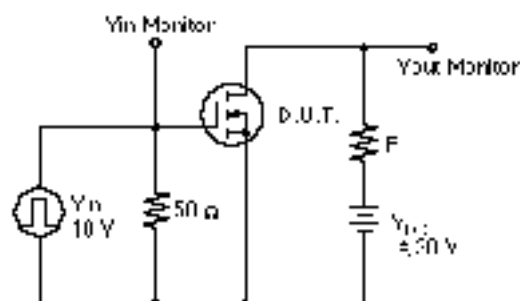
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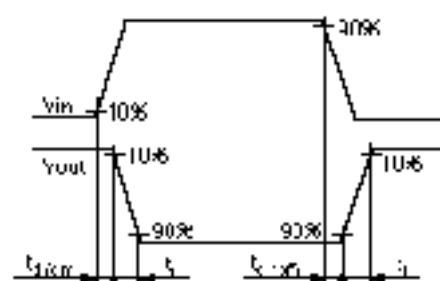
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Switching Time Test Circuit



Waveforms



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Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA 94005-4835

U.S.A.

Tel: 415-589-8000

Fax: 415-589-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dornacher Straße 3

D-85622 Feldkirchen

München

Tel: 089-9 94 80-0

Fax: 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA

United Kingdom

Tel: 0628-585000

Fax: 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel: 535-2100

Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel: 27359218

Fax: 27306074